

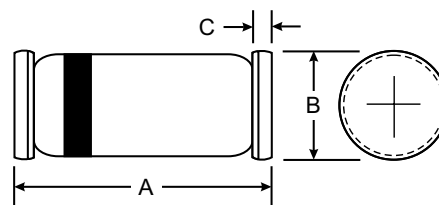


Features

- Saving space
- Hermetic sealed parts
- Micro Melf package

Mechanical Data

- Case: SOD-80/LL34, Glass
- Terminals: Solderable per MIL-STD-202,
- Method 208
- Polarity: Cathode Band
- Weight: 0.05 grams (approx.)



LL34/ SOD-80		
Dim	Min	Max
A	3.30	3.70
B	1.30	1.60
C	0.28	0.50
All Dimensions in mm		

Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise specified

Parameter	Test Conditions	Type	Symbol	Value	Unit
Repetitive peak reverse voltage			V_{RRM}	100	V
Reverse voltage			V_R	75	V
Peak forward surge current	$t_p=1\mu\text{s}$		I_{FSM}	2	A
Repetitive peak forward current			I_{FRM}	450	mA
Forward current			I_F	200	mA
Average forward current	$V_R=0$		I_{FAV}	150	mA
Power dissipation			P_V	500	mW
Junction temperature			T_j	175	$^\circ\text{C}$
Storage temperature range			T_{stg}	-65...+175	$^\circ\text{C}$

Electrical Characteristics $T_j = 25^\circ\text{C}$

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F=5\text{mA}$	MCL4448	V_F	0.62		0.72	V
	$I_F=50\text{mA}$	MCL4148	V_F		0.86	1	V
	$I_F=100\text{mA}$	MCL4448	V_F		0.93	1	V
Reverse current	$V_R=20\text{V}$		I_R			25	nA
	$V_R=20\text{V}, T_j=150^\circ\text{C}$		I_R			50	μA
	$V_R=75\text{V}$		I_R			5	μA
Breakdown voltage	$I_R=100\mu\text{A}, t_p/T=0.01, t_p=0.3\text{ms}$		$V_{(BR)}$	100			V
Diode capacitance	$V_R=0, f=1\text{MHz}, V_{HF}=50\text{mV}$		C_D			4	pF
Rectification efficiency	$V_{HF}=2\text{V}, f=100\text{MHz}$		η_r	45			%
Reverse recovery time	$I_F=I_R=10\text{mA}, i_R=1\text{mA}$		t_{rr}			8	ns
	$I_F=10\text{mA}, V_R=6\text{V}, i_R=0.1 \times I_R, R_L=100\Omega$		t_{rr}			4	ns

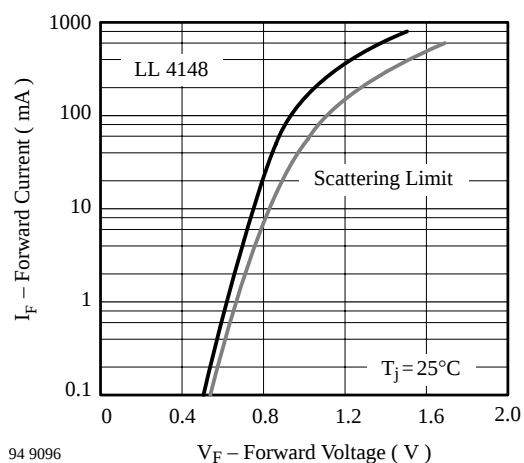


Figure 4. Forward Current vs. Forward Voltage

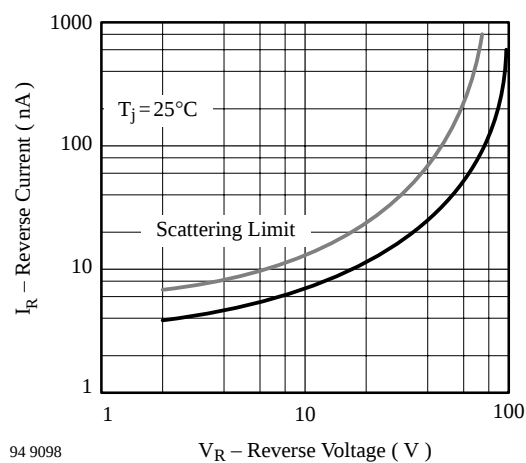


Figure 6. Reverse Current vs. Reverse Voltage

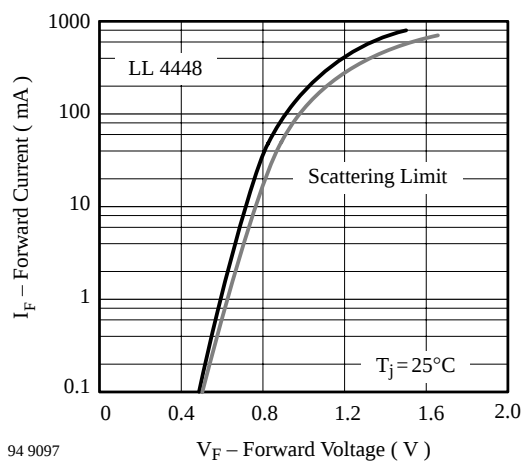


Figure 5. Forward Current vs. Forward Voltage

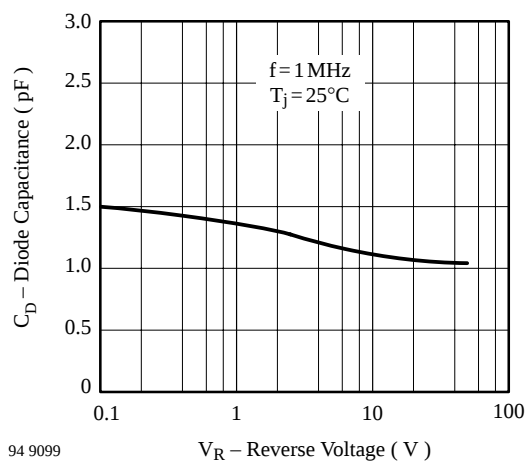


Figure 7. Diode Capacitance vs. Reverse Voltage